

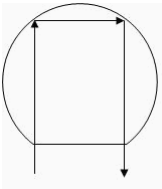
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree
	3.0	Notch or Flat	Notch
	4.0	Secondary Flat Orientation	None
	5.0	Overall Thickness	700.00 +/- 26.00 μ m
	6.0	Total Thickness Variation (TTV)	<10.00 μ m
	7.0	Bow	<80.00 μ m
	8.0	Warp	<80.00 μ m
	9.0	Edge Chips	0
	10.0	Edge Exclusion	5mm
HandleSilicon	11.0	Handle Growth Method	CZ
	12.0	Handle Orientation	{100} +/- 1.0 degree
	13.0	Handle Thickness	675.00 +/- 25.00 μ m
	14.0	Handle Doping Type	P
	15.0	Handle Dopant	Boron
	16.0	Handle Resistivity	0.01 ~ 0.02 Ohmcm
	17.0	Backside Finish	Lapped and etched with poly oxide seal.
BuriedOxide	18.0	Oxide Type	None
DeviceSilicon	19.0	Device Growth Method	FZ
	20.0	Device Orientation	{100} +/- 1.0 degree
	21.0	Nominal Thickness	25.00 +/- 1.00 μ m
	22.0	Distance to device silicon edge from wafer edge	<= 2mm
	23.0	Device Doping Type	P
	24.0	Device Dopant	Boron
	25.0	Device Resistivity	>1000 Ohmcm
	26.0	Voids	none
	27.0	Scratches	10mm maximum length.
	28.0	Haze	none

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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information